

PRESS RELEASE

For Immediate Release

GRANDIS AWARDED THREE KEY STT-RAM PATENTS

New developments advance cell design and further expand patent portfolio for today's and tomorrow's designs

Milpitas, CA, May 9, 2007 – Grandis, Inc., today announced new developments that create a smaller cell size, reduce switching current, and provide higher endurance for its proprietary spin-transfer torque (STT)-RAM technology. Those new developments are based on three key patents issued last March by the U.S. Patent and Trademark Office. These patents bring Grandis' issued U.S. patent total to 22. It has more than 70 patents worldwide issued or pending in STT-RAM technology.

The patents build on other Grandis patents covering innovative magnetic tunnel junction (MTJ) materials and structures including dual MTJ structures. Grandis' continuing stream of new patents not only allows it to offer a complete package to its licensees from magnetic cell structure to circuit and system design, but also assures the availability of the right IP for future STT-RAM generations.

"We are very pleased to add these patents to our STT-RAM patent portfolio," said Yiming Huai, CTO and VP of Engineering of Grandis. "They will further extend our broad and fundamental coverage of STT-RAM technology and enhance our intellectual property and enabling services we offer our licensees."

"Our mission is to make Grandis' STT-RAM enabling technology the number one choice for memory solutions at 45 nm and beyond", said Farhad Tabrizi, Chief Executive Officer of Grandis. "Through our IP licensing and joint development programs, we actively partner with leading semiconductor IDMs, foundries, Fabless and storage technology companies to accelerate STT-RAM commercialization in multiple memory market segments. We believe STT-RAM will become the world's first truly universal memory technology replacing SRAM, NOR, DRAM and eventually NAND flash."

About Grandis, Inc.

Grandis is the pioneer in the development of spin-transfer torque memory (STT-RAM), a universal and scalable memory solution. Grandis licenses its

technology to companies that are developing a variety of products incorporating stand-alone and embedded STT-RAM memory. It offers its licensees a complete range of support services from process installation through qualification. By combining non-volatility and high performance with low power consumption and low cost, STT-RAM can revolutionize the performance of electronic products in many areas. Grandis was established in 2002 and is headquartered in Silicon Valley, California. Investors include Applied Ventures LLC, Sevin Rosen Funds, Matrix Partners, Incubic and Concept Ventures. <http://www.grandisinc.com>

Contact for Grandis, Inc.:

Grandis, Inc.

Corporate Headquarters

1123 Cadillac Court

Milpitas, CA 95035

Tel +1 (408) 945-2160

Fax +1 (408) 945-2161

info@grandisinc.com

Press and Analyst Contact:

Dan Garza

DGPR

dlgarza@dgpr-inc.com

Tel +1 (408) 799-2532